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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I²C, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	23
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 8x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	30-LSSOP (0.240", 6.10mm Width)
Supplier Device Package	30-LSSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f102aagsp-v0

○ ROM, RAM capacities

Code flash	Data flash	RAM	20 pins	24 pins	30 pins
16 KB	2 KB	2 KB	—	—	R5F102AA
	—		—	—	R5F103AA
	2 KB	1.5 KB	R5F1026A Note 1	R5F1027A Note 1	—
	—		R5F1036A Note 1	R5F1037A Note 1	—
12 KB	2KB	1 KB	R5F10269 Note 1	R5F10279 Note 1	R5F102A9
	—		R5F10369 Note 1	R5F10379 Note 1	R5F103A9
8 KB	2 KB	768 B	R5F10268 Note 1	R5F10278 Note 1	R5F102A8
	—		R5F10368 Note 1	R5F10378 Note 1	R5F103A8
4 KB	2KB	512 B	R5F10267	R5F10277	R5F102A7
	—		R5F10367	R5F10377	R5F103A7
2 KB	2 KB	256 B	R5F10266 Note 2	—	—
	—		R5F10366 Note 2	—	—

Notes 1. This is 640 bytes when the self-programming function or data flash function is used. (For details, see **CHAPTER 3 CPU ARCHITECTURE**.)

2. The self-programming function cannot be used for R5F10266 and R5F10366.

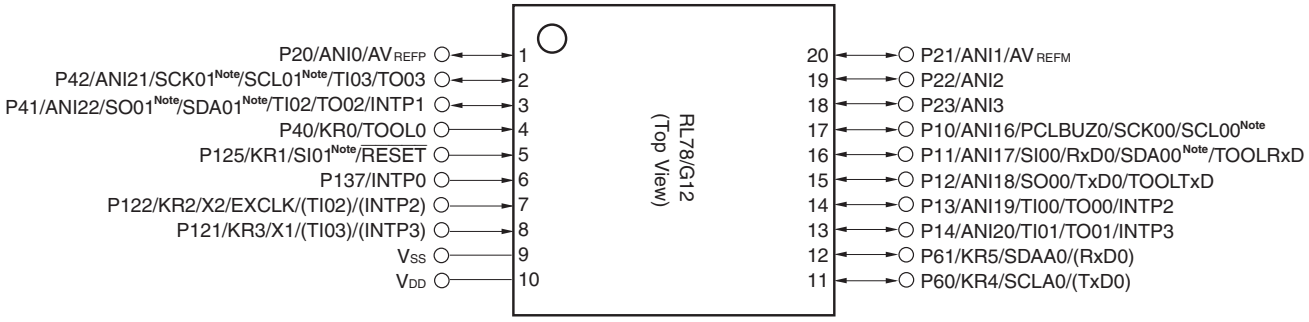
Caution When the flash memory is rewritten via a user program, the code flash area and RAM area are used because each library is used. When using the library, refer to RL78 Family Flash Self Programming Library Type01 User's Manual and RL78 Family Data Flash Library Type04 User's Manual.

1.4 Pin Configuration (Top View)

1.4.1 20-pin products

- 20-pin plastic LSSOP (4.4 × 6.5 mm, 0.65 mm pitch)

<R>



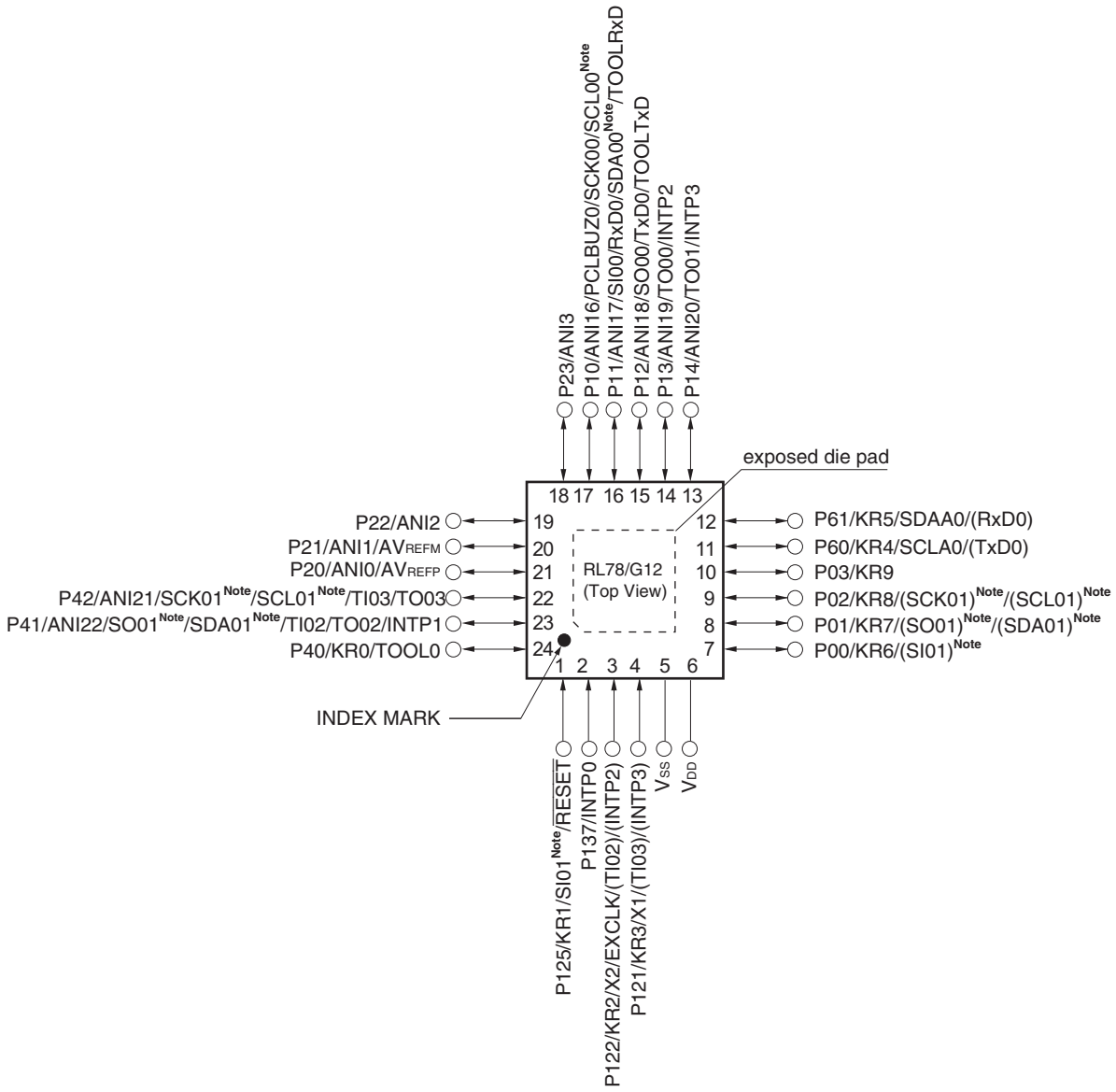
Note Provided only in the R5F102 products.

Remarks 1. For pin identification, see **1.5 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)**.

1.4.2 24-pin products

<R> • 24-pin plastic HWQFN (4 × 4 mm, 0.5 mm pitch)



Note Provided only in the R5F102 products.

Remarks 1. For pin identification, see **1.5 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)**.

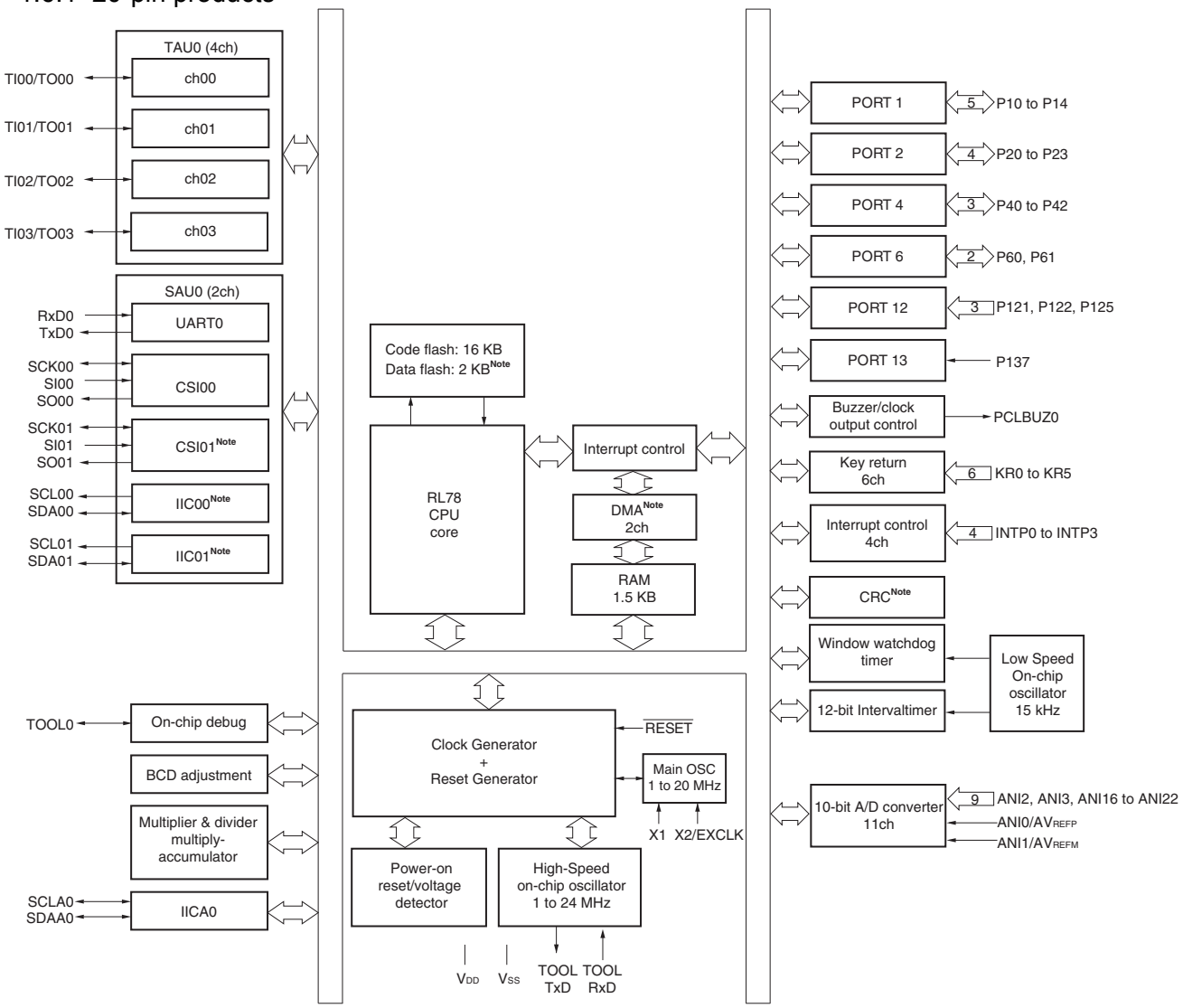
3. It is recommended to connect an exposed die pad to Vss.

1.5 Pin Identification

ANI0 to ANI3, ANI16 to ANI22:	Analog input
AVREFM:	Analog Reference Voltage Minus
AVREFP:	Analog reference voltage plus
EXCLK:	External Clock Input (Main System Clock)
INTP0 to INTP5	Interrupt Request From Peripheral
KR0 to KR9:	Key Return
P00 to P03:	Port 0
P10 to P17:	Port 1
P20 to P23:	Port 2
P30 to P31:	Port 3
P40 to P42:	Port 4
P50, P51:	Port 5
P60, P61:	Port 6
P120 to P122, P125:	Port 12
P137:	Port 13
P147:	Port 14
PCLBUZ0, PCLBUZ1:	Programmable Clock Output/ Buzzer Output
REGC:	Regulator Capacitance
$\overline{\text{RESET}}$:	Reset
RxD0 to RxD2:	Receive Data
SCK00, SCK01, SCK11, SCK20:	Serial Clock Input/Output
SCL00, SCL01, SCL11, SCL20, SCLA0:	Serial Clock Input/Output
SDA00, SDA01, SDA11, SDA20, SDAA0:	Serial Data Input/Output
SI00, SI01, SI11, SI20:	Serial Data Input
SO00, SO01, SO11, SO20:	Serial Data Output
TI00 to TI07:	Timer Input
TO00 to TO07:	Timer Output
TOOL0:	Data Input/Output for Tool
TOOLRxD, TOOLTxD:	Data Input/Output for External Device
TxD0 to TxD2:	Transmit Data
VDD:	Power supply
VSS:	Ground
X1, X2:	Crystal Oscillator (Main System Clock)

1.6 Block Diagram

1.6.1 20-pin products



Note Provided only in the R5F102 products.

(1) 20-, 24-pin products

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(2/2)**

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD2} Note 2	HALT mode	HS (High-speed main) mode Note 6	f_{IH} = 24 MHz Note 4	V_{DD} = 5.0 V		440	1210	μA
					V_{DD} = 3.0 V		440	1210	
				f_{IH} = 16 MHz Note 4	V_{DD} = 5.0 V		400	950	μA
					V_{DD} = 3.0 V		400	950	
			LS (Low-speed main) mode Note 6	f_{IH} = 8 MHz Note 4	V_{DD} = 3.0 V		270	542	μA
					V_{DD} = 2.0 V		270	542	
			HS (High-speed main) mode Note 6	f_{MX} = 20 MHz Note 3, V_{DD} = 5.0 V	Square wave input		280	1000	μA
					Resonator connection		450	1170	
				f_{MX} = 20 MHz Note 3, V_{DD} = 3.0 V	Square wave input		280	1000	μA
					Resonator connection		450	1170	
				f_{MX} = 10 MHz Note 3, V_{DD} = 5.0 V	Square wave input		190	590	μA
					Resonator connection		260	660	
				f_{MX} = 10 MHz Note 3, V_{DD} = 3.0 V	Square wave input		190	590	μA
					Resonator connection		260	660	
			LS (Low-speed main) mode Note 6	f_{MX} = 8 MHz Note 3, V_{DD} = 3.0 V	Square wave input		110	360	μA
					Resonator connection		150	416	
				f_{MX} = 8 MHz Note 3, V_{DD} = 2.0 V	Square wave input		110	360	μA
					Resonator connection		150	416	
	I_{DD3} Note 5	STOP mode	T_A = –40°C				0.19	0.50	μA
			T_A = +25°C				0.24	0.50	
			T_A = +50°C				0.32	0.80	
			T_A = +70°C				0.48	1.20	
			T_A = +85°C				0.74	2.20	

Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. During HALT instruction execution by flash memory.

3. When high-speed on-chip oscillator clock is stopped.

4. When high-speed system clock is stopped.

5. Not including the current flowing into the 12-bit interval timer and watchdog timer.

6. Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS(High speed main) mode: V_{DD} = 2.7 V to 5.5 V @1 MHz to 24 MHz
V_{DD} = 2.4 V to 5.5 V @1 MHz to 16 MHz

LS(Low speed main) mode: V_{DD} = 1.8 V to 5.5 V @1 MHz to 8 MHz

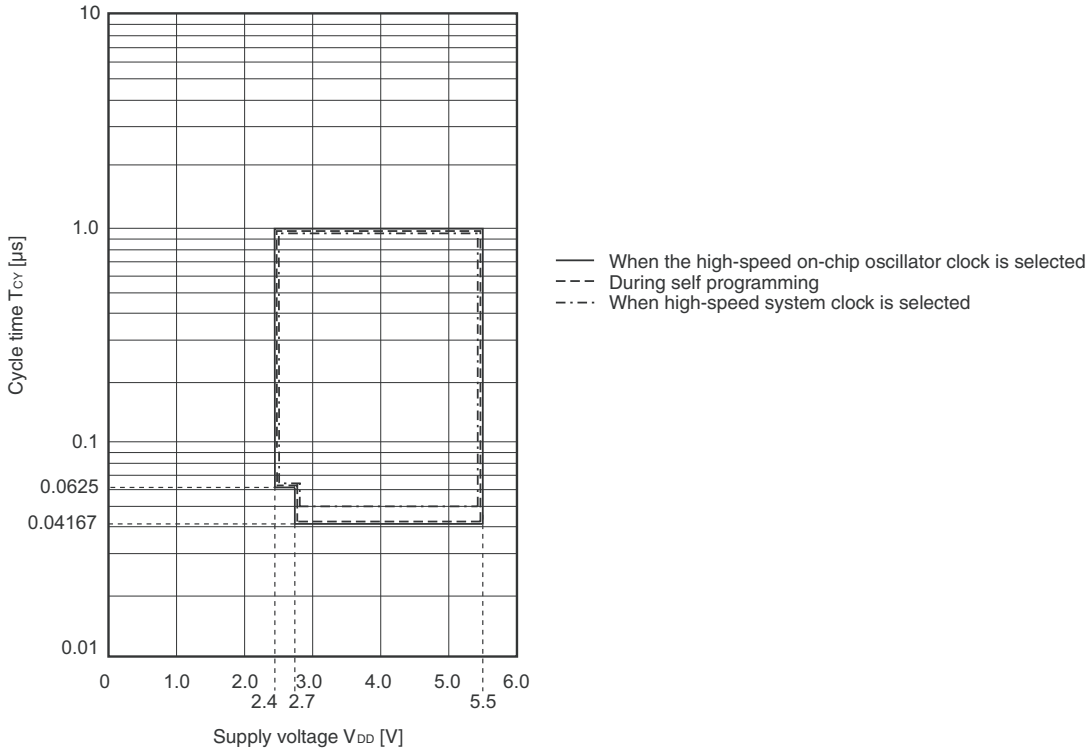
Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH}: high-speed on-chip oscillator clock frequency

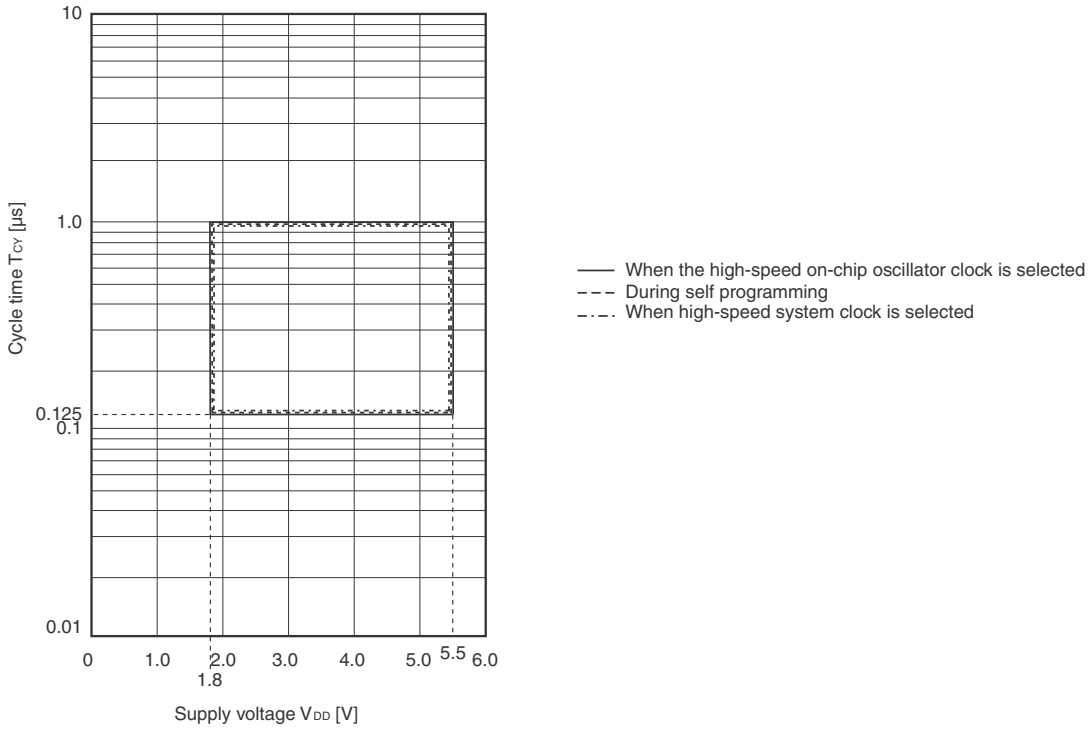
3. Except temperature condition of the TYP. value is T_A = 25°C, other than STOP mode

Minimum Instruction Execution Time during Main System Clock Operation

T_{CY} vs V_{DD} (HS (high-speed main) mode)



T_{CY} vs V_{DD} (LS (low-speed main) mode)



(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)

(T_A = −40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note4	t_{KCY2}	4.0 V ≤ V_{DD} ≤ 5.5 V	20 MHz < f_{MCK}	8/f_{MCK}		–		ns
			f_{MCK} ≤ 20 MHz	6/f_{MCK}		6/f_{MCK}		ns
		2.7 V ≤ V_{DD} ≤ 5.5 V	16 MHz < f_{MCK}	8/f_{MCK}		–		ns
			f_{MCK} ≤ 16 MHz	6/f_{MCK}		6/f_{MCK}		ns
		2.4 V ≤ V_{DD} ≤ 5.5 V		6/f_{MCK} and 500		6/f_{MCK} and 500		ns
		1.8 V ≤ V_{DD} ≤ 5.5 V		–		6/f_{MCK} and 750		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	4.0 V ≤ V_{DD} ≤ 5.5 V		t_{KCY2}/2−7		t_{KCY2}/2−7		ns
		2.7 V ≤ V_{DD} ≤ 5.5 V		t_{KCY2}/2−8		t_{KCY2}/2−8		ns
		2.4 V ≤ V_{DD} ≤ 5.5 V		t_{KCY2}/2−18		t_{KCY2}/2−18		ns
		1.8 V ≤ V_{DD} ≤ 5.5 V		–		t_{KCY2}/2−18		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK2}	2.7 V ≤ V_{DD} ≤ 5.5 V		1/f_{MCK} + 20		1/f_{MCK} + 30		ns
		2.4 V ≤ V_{DD} ≤ 5.5 V		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		1.8 V ≤ V_{DD} ≤ 5.5 V		–		1/f_{MCK} + 30		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI2}			1/f_{MCK} + 31		1/f_{MCK} + 31		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO2}	C = 30 pF Note4	2.7 V ≤ V_{DD} ≤ 5.5 V		2/f_{MCK} + 44		2/f_{MCK} + 110	ns
			2.4 V ≤ V_{DD} ≤ 5.5 V		2/f_{MCK} + 75		2/f_{MCK} + 110	ns
			1.8 V ≤ V_{DD} ≤ 5.5 V		–		2/f_{MCK} + 110	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

4. C is the load capacitance of the SOp output lines.

5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

Caution Select the normal input buffer for the SIp and SCKp pins and the normal output mode for the SOp pin by using port input mode register 1 (PIM1) and port output mode registers 0, 1, 4 (POM0, POM1, POM4).

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)

(T_A = −40 to +85°C, 1.8 V ≤ V_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq 4/f_{CLK}$	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	300		1150		ns
			2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	500		1150		ns
			1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note, C_b = 30 pF, R_b = 5.5 kΩ	1150		1150		ns
SCKp high-level width	t_{KH1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		t_{KCY1}/2 −75		t_{KCY1}/2−75		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 −170		t_{KCY1}/2−170		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note, C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 −458		t_{KCY1}/2−458		ns
SCKp low-level width	t_{KL1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		t_{KCY1}/2 −12		t_{KCY1}/2−50		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 −18		t_{KCY1}/2−50		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note, C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 −50		t_{KCY1}/2−50		ns

Note Use it with $V_{DD} \geq V_b$.

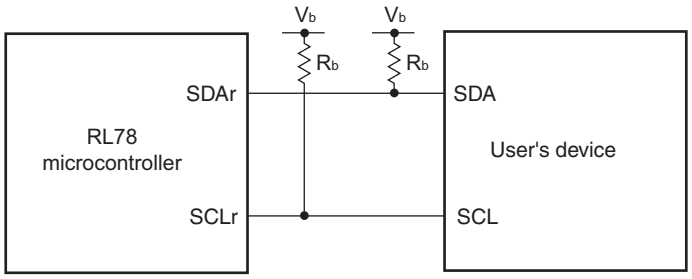
Cautions 1. Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

2. CSI01 and CSI11 cannot communicate at different potential.

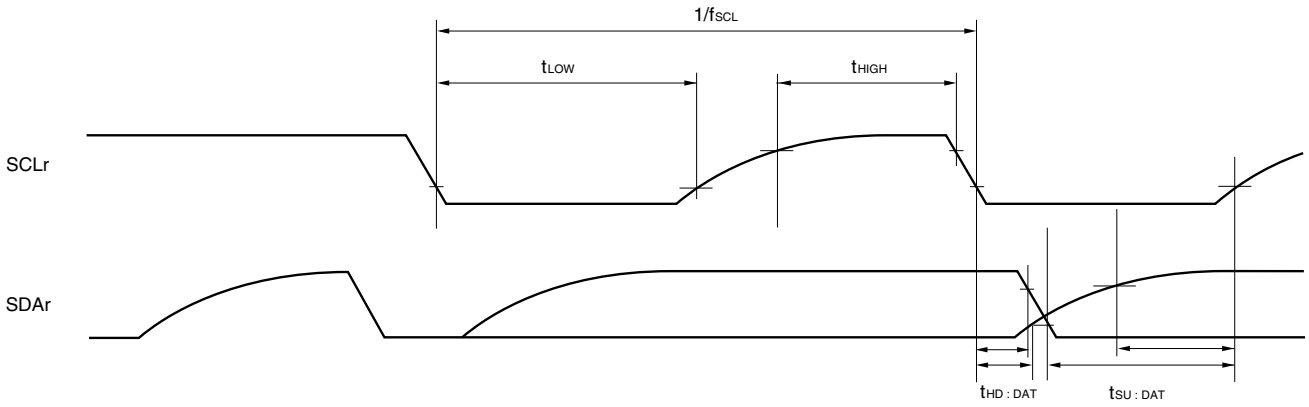
Remarks 1. R_b [Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b [F]: Communication line (SCKp, SOp) load capacitance, V_b [V]: Communication line voltage

2. p: CSI number (p = 00, 20)

Simplified I^2C mode connection diagram (during communication at different potential)



Simplified I^2C mode serial transfer timing (during communication at different potential)



Remarks 1. R_b [Ω]: Communication line (SDAr, SCLr) pull-up resistance, C_b [F]: Communication line (SDAr, SCLr) load capacitance, V_b [V]: Communication line voltage

2. r: IIC Number (r = 00, 20)

3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number (m = 0,1), n: Channel number (n = 0))

4. Simplified I^2C mode is supported only by the R5F102 products.

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel	Reference Voltage		
	Reference voltage (+) = AV_{REFP} Reference voltage (–) = AV_{REFM}	Reference voltage (+) = V_{DD} Reference voltage (–) = V_{SS}	Reference voltage (+) = V_{BGR} Reference voltage (–) = AV_{REFM}
ANI0 to ANI3	Refer to **28.6.1 (1)**.	Refer to **28.6.1 (3)**.	Refer to **28.6.1 (4)**.
ANI16 to ANI22	Refer to **28.6.1 (2)**.		
Internal reference voltage Temperature sensor output voltage	Refer to **28.6.1 (1)**.		–

(1) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (–) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI2, ANI3, internal reference voltage, and temperature sensor output voltage

(T_A = –40 to +85°C, 1.8 V ≤ AV_{REFP} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (–) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error[Note 1]	AINL	10-bit resolution AV_{REFP} = V_{DD} [Note 3]			1.2	±3.5	LSB
					1.2	±7.0 [Note 4]	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI2, ANI3	3.6 V ≤ V_{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
				57		95	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V_{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error[Notes 1, 2]	EZS	10-bit resolution AV_{REFP} = V_{DD} [Note 3]				±0.25	%FSR
						±0.50 [Note 4]	%FSR
Full-scale error[Notes 1, 2]	EFS	10-bit resolution AV_{REFP} = V_{DD} [Note 3]				±0.25	%FSR
						±0.50 [Note 4]	%FSR
Integral linearity error[Note 1]	ILE	10-bit resolution AV_{REFP} = V_{DD} [Note 3]				±2.5	LSB
						±5.0 [Note 4]	LSB
Differential linearity error [Note 1]	DLE	10-bit resolution AV_{REFP} = V_{DD} [Note 3]				±1.5	LSB
						±2.0 [Note 4]	LSB
Analog input voltage	V_{AIN}	ANI2, ANI3		0		AV_{REFP}	V
		Internal reference voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{BGR} [Note 5]			V
		Temperature sensor output voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{TMPS25} [Note 5]			V

(**Notes** are listed on the next page.)

2.6.4 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

(T_A = –40 to +85°C, $V_{PDR} \leq V_{DD} \leq 5.5$ V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection supply voltage	V_{LVD0}	Power supply rise time	3.98	4.06	4.14	V
		Power supply fall time	3.90	3.98	4.06	V
	V_{LVD1}	Power supply rise time	3.68	3.75	3.82	V
		Power supply fall time	3.60	3.67	3.74	V
	V_{LVD2}	Power supply rise time	3.07	3.13	3.19	V
		Power supply fall time	3.00	3.06	3.12	V
	V_{LVD3}	Power supply rise time	2.96	3.02	3.08	V
		Power supply fall time	2.90	2.96	3.02	V
	V_{LVD4}	Power supply rise time	2.86	2.92	2.97	V
		Power supply fall time	2.80	2.86	2.91	V
	V_{LVD5}	Power supply rise time	2.76	2.81	2.87	V
		Power supply fall time	2.70	2.75	2.81	V
	V_{LVD6}	Power supply rise time	2.66	2.71	2.76	V
		Power supply fall time	2.60	2.65	2.70	V
	V_{LVD7}	Power supply rise time	2.56	2.61	2.66	V
		Power supply fall time	2.50	2.55	2.60	V
	V_{LVD8}	Power supply rise time	2.45	2.50	2.55	V
		Power supply fall time	2.40	2.45	2.50	V
	V_{LVD9}	Power supply rise time	2.05	2.09	2.13	V
		Power supply fall time	2.00	2.04	2.08	V
	V_{LVD10}	Power supply rise time	1.94	1.98	2.02	V
		Power supply fall time	1.90	1.94	1.98	V
	V_{LVD11}	Power supply rise time	1.84	1.88	1.91	V
		Power supply fall time	1.80	1.84	1.87	V
Minimum pulse width	t_{LW}		300			μs
Detection delay time					300	μs

3.1 Absolute Maximum Ratings

Absolute Maximum Ratings (T_A = 25°C)

Parameter	Symbols	Conditions		Ratings	Unit
Supply Voltage	V_{DD}			−0.5 to + 6.5	V
REGC terminal input voltage[Note1]	V_{IREGC}	REGC		−0.3 to +2.8 and −0.3 to V_{DD} + 0.3 [Note 2]	V
Input Voltage	V_{I1}	Other than P60, P61		−0.3 to V_{DD} + 0.3[Note 3]	V
	V_{I2}	P60, P61 (N-ch open drain)		−0.3 to 6.5	V
Output Voltage	V_O			−0.3 to V_{DD} + 0.3[Note 3]	V
Analog input voltage	V_{AI}	20, 24-pin products: ANI0 to ANI3, ANI16 to ANI22 30-pin products: ANI0 to ANI3, ANI16 to ANI19		−0.3 to V_{DD} + 0.3 and −0.3 to AVREF(+)+0.3 [Notes 3, 4]	V
Output current, high	I_{OH1}	Per pin	Other than P20 to P23	−40	mA
		Total of all pins	All the terminals other than P20 to P23	−170	mA
			20-, 24-pin products: P40 to P42 30-pin products: P00, P01, P40, P120	−70	mA
			20-, 24-pin products: P00 to P03[Note 5], P10 to P14 30-pin products: P10 to P17, P30, P31, P50, P51, P147	−100	mA
	I_{OH2}	Per pin	P20 to P23	−0.5	mA
		Total of all pins		−2	mA
Output current, low	I_{OL1}	Per pin	Other than P20 to P23	40	mA
		Total of all pins	All the terminals other than P20 to P23	170	mA
			20-, 24-pin products: P40 to P42 30-pin products: P00, P01, P40, P120	70	mA
			20-, 24-pin products: P00 to P03 [Note 5], P10 to P14, P60, P61 30-pin products: P10 to P17, P30, P31, P50, P51, P60, P61, P147	100	mA
	I_{OL2}	Per pin	P20 to P23	1	mA
		Total of all pins		5	mA
Operating ambient temperature	T_A			−40 to +105	°C
Storage temperature	T_{stg}			−65 to +150	°C

Notes 1. 30-pin product only.

2. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μF). This value determines the absolute maximum rating of the REGC pin. Do not use it with voltage applied.

3. Must be 6.5 V or lower.

4. Do not exceed $AV_{REF}(+)$ + 0.3 V in case of A/D conversion target pin.

5. 24-pin products only.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remarks 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2. $AV_{REF}(+)$: + side reference voltage of the A/D converter.

3. V_{SS} : Reference voltage

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) (3/4)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V_{IH1}	Normal input buffer 20-, 24-pin products: P00 to P03[Note 2], P10 to P14, P40 to P42 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147		0.8V_{DD}		V_{DD}	V
	V_{IH2}	TTL input buffer 20-, 24-pin products: P10, P11 30-pin products: P01, P10, P11, P13 to P17	4.0 V ≤ V_{DD} ≤ 5.5 V	2.2		V_{DD}	V
			3.3 V ≤ V_{DD} < 4.0 V	2.0		V_{DD}	V
			2.4 V ≤ V_{DD} < 3.3 V	1.5		V_{DD}	V
	V_{IH3}	Normal input buffer P20 to P23		0.7V_{DD}		V_{DD}	V
	V_{IH4}	P60, P61		0.7V_{DD}		6.0	V
	V_{IH5}	P121, P122, P125[Note 1], P137, EXCLK, $\overline{\text{RESET}}$		0.8V_{DD}		V_{DD}	V
Input voltage, low	V_{IL1}	Normal input buffer 20-, 24-pin products: P00 to P03[Note 2], P10 to P14, P40 to P42 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147		0		0.2V_{DD}	V
	V_{IL2}	TTL input buffer 20-, 24-pin products: P10, P11 30-pin products: P01, P10, P11, P13 to P17	4.0 V ≤ V_{DD} ≤ 5.5 V	0		0.8	V
			3.3 V ≤ V_{DD} < 4.0 V	0		0.5	V
			2.4 V ≤ V_{DD} < 3.3 V	0		0.32	V
	V_{IL3}	P20 to P23		0		0.3V_{DD}	V
	V_{IL4}	P60, P61		0		0.3V_{DD}	V
	V_{IL5}	P121, P122, P125[Note 1], P137, EXCLK, $\overline{\text{RESET}}$		0		0.2V_{DD}	V
Output voltage, high	V_{OH1}	20-, 24-pin products: P00 to P03[Note 2], P10 to P14, P40 to P42 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147	4.0 V ≤ V_{DD} ≤ 5.5 V, I_{OH1} = –3.0 mA	V_{DD}–0.7			V
			2.7 V ≤ V_{DD} ≤ 5.5 V, I_{OH1} = –2.0 mA	V_{DD}–0.6			V
			2.4 V ≤ V_{DD} ≤ 5.5 V, I_{OH1} = –1.5 mA	V_{DD}–0.5			V
	V_{OH2}	P20 to P23	I_{OH2} = –100 μA	V_{DD}–0.5			V

Notes 1. 20, 24-pin products only.

2. 24-pin products only.

Caution The maximum value of V_{IH} of pins P10 to P12 and P41 for 20-pin products, P01, P10 to P12, and P41 for 24-pin products, and P00, P10 to P15, P17, and P50 for 30-pin products is V_{DD} even in N-ch open-drain mode. High level is not output in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

3.4 AC Characteristics

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T_{CY}	Main system clock (f_{MAIN}) operation	HS (High-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.04167		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
		During self programming	HS (High-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.04167		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
External main system clock frequency	f_{EX}	2.7 V ≤ V_{DD} ≤ 5.5 V			1.0		20.0	MHz
		2.4 V ≤ V_{DD} < 2.7 V			1.0		16.0	MHz
External main system clock input high-level width, low-level width	t_{EXH}, t_{EXL}	2.7 V ≤ V_{DD} ≤ 5.5 V			24			ns
		2.4 V ≤ V_{DD} < 2.7 V			30			ns
TI00 to TI07 input high-level width, low-level width	t_{TIH}, t_{TIL}				1/f_{MCK} + 10			ns
TO00 to TO07 output frequency	f_{TO}	4.0 V ≤ V_{DD} ≤ 5.5 V					12	MHz
		2.7 V ≤ V_{DD} < 4.0 V					8	MHz
		2.4 V ≤ V_{DD} < 2.7 V					4	MHz
PCLBUZ0, or PCLBUZ1 output frequency	f_{PCL}	4.0 V ≤ V_{DD} ≤ 5.5 V					16	MHz
		2.7 V ≤ V_{DD} < 4.0 V					8	MHz
		2.4 V ≤ V_{DD} < 2.7 V					4	MHz
INTP0 to INTP5 input high-level width, low-level width	t_{INTH}, t_{INTL}				1			μs
KR0 to KR9 input available width	t_{KR}				250			ns
$\overline{\text{RESET}}$ low-level width	t_{RSL}				10			μs

Remark f_{MCK}: Timer array unit operation clock frequency
(Operation clock to be set by the timer clock select register 0 (TPS0) and the CKS0n bit of timer mode register 0n (TMR0n). n: Channel number (n = 0 to 7))

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100\ [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

4. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to **Note 3** above to calculate the maximum transfer rate under conditions of the customer.

5. The smaller maximum transfer rate derived by using f_{MCK}/12 or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 2.7 V ≤ V_{DD} < 4.0 V and 2.3 V ≤ V_b ≤ 2.7 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3}\ [\text{bps}]$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100\ [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

6. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to **Note 5** above to calculate the maximum transfer rate under conditions of the customer.

7. The smaller maximum transfer rate derived by using f_{MCK}/12 or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3}\ [\text{bps}]$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100\ [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

8. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to **Note 7** above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). **For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.**

(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)
(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time Note 1	t_{KCY2}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V	20 MHz < f_{MCK} ≤ 24 MHz	24/f_{MCK}		ns
			8 MHz < f_{MCK} ≤ 20 MHz	20/f_{MCK}		ns
			4 MHz < f_{MCK} ≤ 8 MHz	16/f_{MCK}		ns
			f_{MCK} ≤ 4 MHz	12/f_{MCK}		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V	20 MHz < f_{MCK} ≤ 24 MHz	32/f_{MCK}		ns
			16 MHz < f_{MCK} ≤ 20 MHz	28/f_{MCK}		ns
			8 MHz < f_{MCK} ≤ 16 MHz	24/f_{MCK}		ns
			4 MHz < f_{MCK} ≤ 8 MHz	16/f_{MCK}		ns
			f_{MCK} ≤ 4 MHz	12/f_{MCK}		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V	20 MHz < f_{MCK} ≤ 24 MHz	72/f_{MCK}		ns
			16 MHz < f_{MCK} ≤ 20 MHz	64/f_{MCK}		ns
			8 MHz < f_{MCK} ≤ 16 MHz	52/f_{MCK}		ns
			4 MHz < f_{MCK} ≤ 8 MHz	32/f_{MCK}		ns
			f_{MCK} ≤ 4 MHz	20/f_{MCK}		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V		t_{KCY2}/2 – 24		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V		t_{KCY2}/2 – 36		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		t_{KCY2}/2 – 100		ns
SIp setup time (to SCKp↑) Note 2	t_{SIK2}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_{DD} ≤ 4.0 V		1/f_{MCK} + 40		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V		1/f_{MCK} + 40		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_{DD} ≤ 2.0 V		1/f_{MCK} + 60		ns
SIp hold time (from SCKp↑) Note 3	t_{KSI2}			1/f_{MCK} + 62		ns
Delay time from SCKp↓ to SOp output Note 4	t_{KSO2}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ			2/f_{MCK} + 240	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ			2/f_{MCK} + 428	ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ			2/f_{MCK} + 1146	ns

Notes 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Cautions 1. Select the TTL input buffer for the SIp and SCKp pins and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). **For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.**

2. CSI01 and CSI11 cannot communicate at different potential.

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I^2C mode)

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	f_{SCL}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ		100 Note1	kHz
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ		100 Note1	kHz
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 100 pF, R_b = 5.5 kΩ		100 Note1	kHz
Hold time when SCLr = "L"	t_{LOW}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	4600		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	4600		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 100 pF, R_b = 5.5 kΩ	4650		ns
Hold time when SCLr = "H"	t_{HIGH}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	2700		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	2400		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 100 pF, R_b = 5.5 kΩ	1830		ns
Data setup time (reception)	$t_{SU:DAT}$	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	1/f_{MCK} + 760 Note3		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	1/f_{MCK} + 760 Note3		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 100 pF, R_b = 5.5 kΩ	1/f_{MCK} + 570 Note3		ns
Data hold time (transmission)	$t_{HD:DAT}$	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	0	1420	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	0	1420	ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 100 pF, R_b = 5.5 kΩ	0	1215	ns

Notes 1. The value must also be equal to or less than f_{MCK}/4.

2. Set $t_{SU:DAT}$ so that it will not exceed the hold time when SCLr = "L" or SCLr = "H".

Cautions 1. Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance) mode for the SCLr pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

2. IIC01 and IIC11 cannot communicate at different potential.

(**Remarks** are listed on the next page.)

Rev.	Date	Description	
		Page	Summary
2.00	Sep 06, 2013	55	Modification of description and Notes 3 and 4 in 2.6.1 (3)
		56	Modification of description and Notes 3 and 4 in 2.6.1 (4)
		57	Modification of table in 2.6.2 Temperature sensor/internal reference voltage characteristics
		57	Modification of table and Note in 2.6.3 POR circuit characteristics
		58	Modification of table in 2.6.4 LVD circuit characteristics
		59	Modification of table of LVD detection voltage of interrupt & reset mode
		59	Modification of number and title to 2.6.5 Power supply voltage rising slope characteristics
		61	Modification of table, figure, and Remark in 2.10 Timing of Entry to Flash Memory Programming Modes
		62 to 103	Addition of products of industrial applications (G: T_A = -40 to +105°C)
		104 to 106	Addition of products of industrial applications (G: T_A = -40 to +105°C)
2.10	Mar 25, 2016	6	Modification of Figure 1-1 Part Number, Memory Size, and Package of RL78/G12
		7	Modification of Table 1-1 List of Ordering Part Numbers
		8	Addition of product name (RL78/G12) and description (Top View) in 1.4.1 20-pin products
		9	Addition of product name (RL78/G12) and description (Top View) in 1.4.2 24-pin products
		10	Addition of product name (RL78/G12) and description (Top View) in 1.4.3 30-pin products
		15	Modification of description in 1.7 Outline of Functions
		16	Modification of description, and addition of target products
		52	Modification of note 2 in 2.5.2 Serial interface IICA
		60	Modification of title and note, and addition of caution in 2.7 RAM Data Retention Characteristics
		60	Modification of conditions in 2.8 Flash Memory Programming Characteristics
		62	Modification of description, and addition of target products and remark
		94	Modification of note 2 in 3.5.2 Serial interface IICA
		102	Modification of title and note in 3.7 RAM Data Retention Characteristics
		102	Modification of conditions in 3.8 Flash Memory Programming Characteristics
		104 to 106	Addition of package name

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